Process integration and structural characterization of three−stacked gate−all−around nanosheet pFETs

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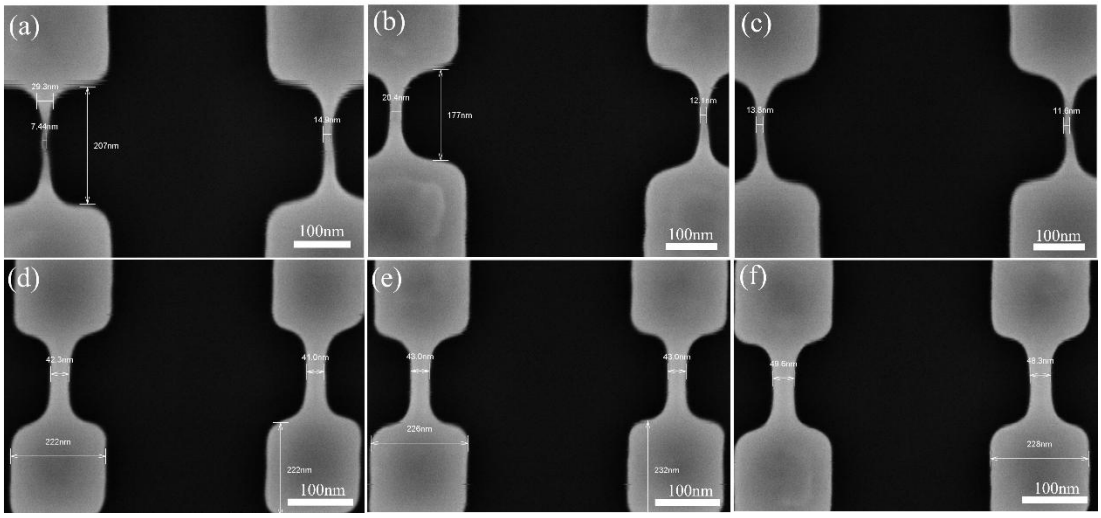

Fig. S1. Cross-sectional SEM images of anisotropically etched stacked nanosheets (a-f) with width labels. All scale bars: 100 nm.